

ABSTRACT OF THE DISCLOSURE

A thin film transistor including:
an insulating layer;
a gate electrode;
a semiconductor layer including coalesced structurally ordered polymer aggregates of a self-organizable polymer, wherein the self-organizable polymer is of a type capable of gelling;
a source electrode; and
a drain electrode,
wherein the insulating layer, the gate electrode, the semiconductor layer, the source electrode, and the drain electrode are in any sequence as long as the gate electrode and the semiconductor layer both contact the insulating layer, and the source electrode and the drain electrode both contact the semiconductor layer.